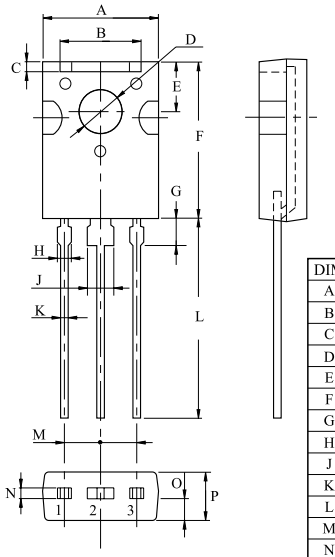
KTA1703

EPITAXIAL PLANAR PNP TRANSISTOR

HIGH VOLTAGE APPLICATION.
DC-DC CONVERTER.
LOW POWER SWITCHING REGULATOR.

FEATURES

- High Breakdown Voltage.
  : V_{CEO}=-400V
- Low Collector Saturation Voltage
  : $V_{CE(sat)}$=-1V(max.), (I_C=-100mA, I_B=-10mA)
- High Speed Switching.



DIM	MILLIMETERS
A	8.3 MAX
B	5.8
C	0.7
D	Φ3.2±0.1
E	3.5
F	11.0±0.3
G	2.9 MAX
H	1.0 MAX
J	1.9 MAX
K	0.75±0.15
L	15.50±0.5
M	2.3±0.1
N	0.65±0.15
O	1.6
P	3.4 MAX

1. EMITTER
2. COLLECTOR
3. BASE

TO-126

MAXIMUM RATING (Ta=25℃)

CHARACTERISTIC		SYMBOL	RATING	UNIT
Collector-Base Voltage		V_{CBO}	-400	V
Collector-Emitter Voltage		V_{CEO}	-400	V
Emitter-Base Voltage		V_{EBO}	-7	V
Collector Current	DC	I_C	-0.5	A
	Pulse	I_{CP}	-1	
Base Current		I_B	-0.25	A
Collector Power Dissipation	Ta=25℃	P_C	1.5W	W
	Tc=25℃		15W	
Junction Temperature		T_j	150	℃
Storage Temperature		T_{stg}	-55 150	℃

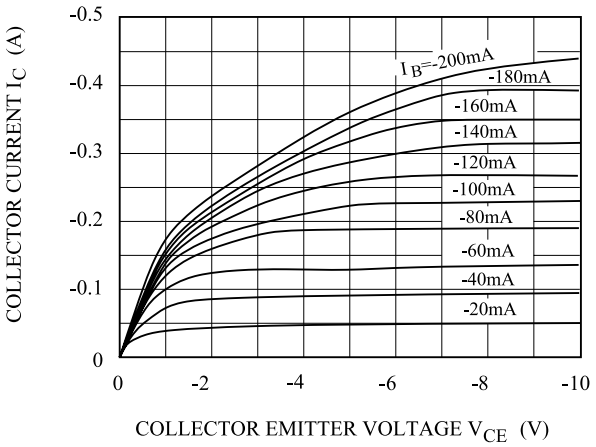
Not recommended for new design

ELECTRICAL CHARACTERISTICS (Ta=25℃)

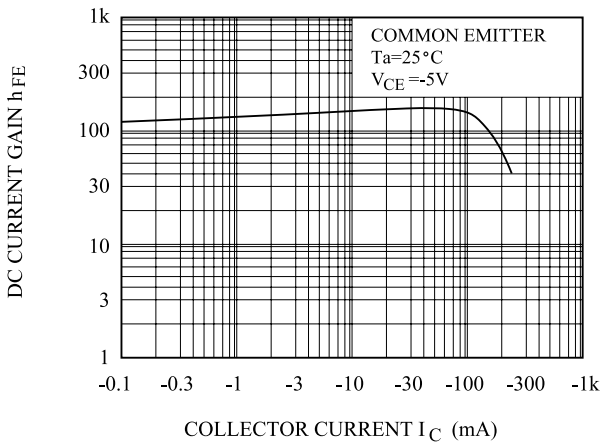
CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Base Voltage		$V_{(BR)CBO}$	I_C=-100 μA, I_E=0	-400	-	-	V
Collector Emitter Voltage		$V_{(BR)CEO}$	I_C=-1mA, I_B=0	-400	-	-	
Collector Cutoff Current		I_{CBO}	V_{CB}=-400V, I_E=0	-	-	-10	μA
Emitter Cutoff Current		I_{EBO}	V_{EB}=-5V, I_C=0	-	-	-10	
DC Current Gain		h_{FE} (Note)	V_{CE}=-5V, I_C=-100mA	60	-	200	-
Collector-Emitter Saturation Voltage		$V_{CE(sat)}$	I_C=-100mA, I_B=-10mA	-	-	-1	V
Base-Emitter Saturation Voltage		$V_{BE(sat)}$	I_C=-100mA, I_B=-10mA	-	-	-1.2	
Switching Time	Turn On Time	t_{ON}	I_C=-100mA, R_L=1.5kΩ	-	-	1	μS
	Storage Time	t_{stg}	I_{B1}=-10mA, I_{B2}=20mA	-	-	4	
	Fall Time	t_f	V_{CC}=-150V	-	-	1	

Note : h_{FE} Classification O:60 120, Y:100 200

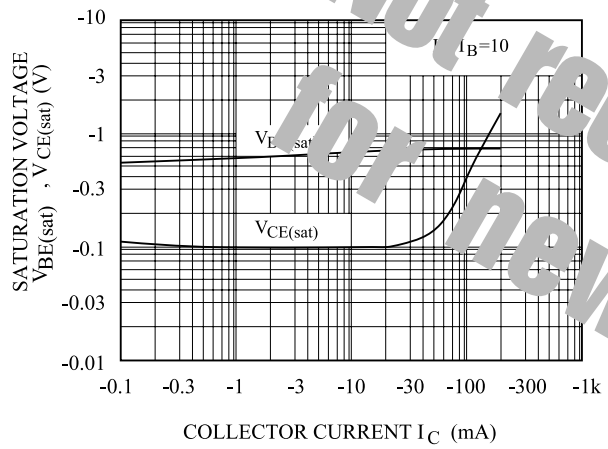
I_C - V_{CE}



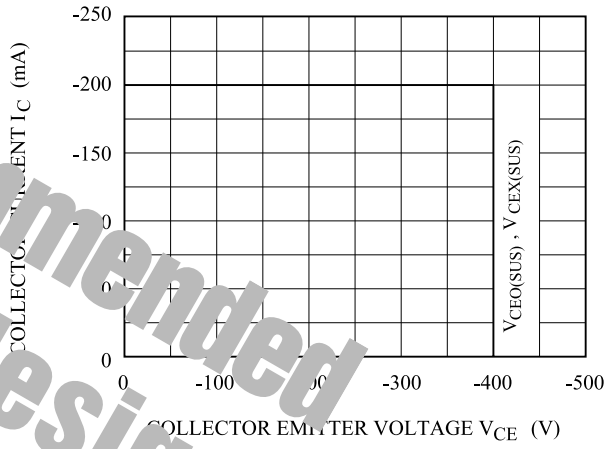
h_{FE} - I_C



$V_{BE(sat)}$, $V_{CE(sat)}$ - I_C

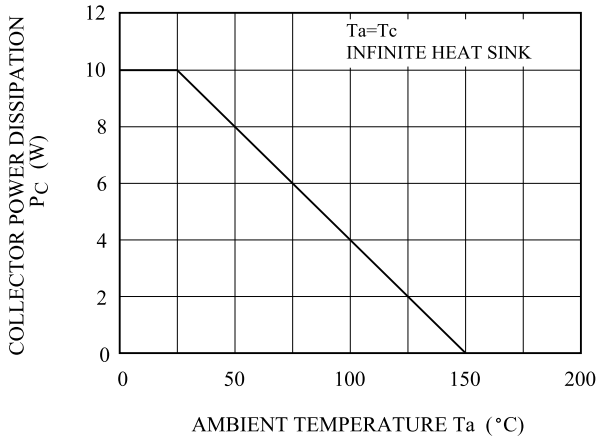


REVERSE BIAS SAFE OPERATING AREA



Not recommended for new design

Pc - Ta



SAFE OPERATING AREA